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## PATENT ABSTRACTS OF JAPAN

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**(54) DEPOSITION FILM  
FORMING METHOD**

(57) Abstract:

**PURPOSE:** To enable to form a thick deposition film of large area by a method wherein exciting energy is obtained using a specific annular silane compound, and a deposition film containing silicon atoms is formed using low level heat energy.

**CONSTITUTION:** Pertaining to a method wherein the excitation and decompositional condition of raw gas are formed by giving heat energy and, especially, an amorphous silicon (a-Si) deposition film is formed on a specific supporting member, an a-Si deposition film can be formed with low energy level and high film-forming speed using the annular silane compound in the mixed condition with a halogenide as the raw gas to be decomposed by heat energy, which is indicated by a general formula (provided that the n in the above-mentioned formula indicates 3, 4 or 5, and R indicates H or SiH<sub>3</sub>). Also, the a-Si deposition film which is excellent in uniformity of optical characteristics and stability in quality can be formed. Said deposition film is formed inside a deposition chamber 1.

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